

CE1N2R

on-chip resistor NPN silicon epitaxial transistor For mid-speed switching

The CE1N2R is a transistor of on-chip high hFE resistor incorporating dumper diode in collector to emitter and zener diode in collector to base as protect elements. This transistor is ideal for actuator drives of OA equipments and electric equipments.

FEATURES

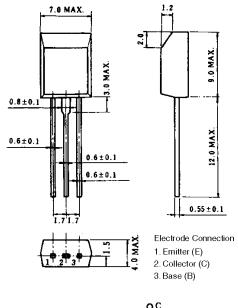
- On-chip zener diode for surge voltage absorption
- On-chip bias resistor: $R_1 = 680 \Omega$, $R_2 = 10 k\Omega$
- Low power consumption during driving:
 Vol = 0.3 V MAX.@V1 = 5.0 V, Ic = 0.5 A
- On-chip dumper diode for reverse cable

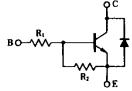
ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vcво	60±10	V
Collector to emitter voltage	VCEO	60±10	٧
Emitter to base voltage	V _{EBO}	15	٧
Collector current (DC)	Ic(DC)	±2.0	Α
Collector current (Pulse)	I _{C(pulse)} *	±3.0	Α
Base current (DC)	I _{B(DC)}	0.03	Α
Total power dissipation	Рт	1.0	W
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

^{*} PW \leq 10 ms, duty cycle \leq 50 %

PACKAGE DRAWING (UNIT: mm)





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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Colletor to emitter voltage	VCEO(SUS)	Ic = 2.0 A, Iв = 5.0 mA, L = 6.0 mH	50	60		V
Collector cutoff current	Ісво	V _{CB} = 40 V, I _E = 0			100	nA
DC current gain	h _{FE1} **	Vce = 5.0 V, Ic = 0.2 A	700	1200		-
DC current gain	hFE2 **	Vce = 5.0 V, Ic = 1.0 A	1000	1700	3000	-
DC current gain	h _{FE3} **	VcE = 5.0 V, Ic = 2.0 A	500	1300		-
Low level output voltage	Vol **	V _I = 5.0 V, Ic = 0.5 A		0.12	0.3	V
Low level input voltage	VIL **	Vcε = 12 V, Ic = 100 μA		0.43	0.4	V
Input resistance	R ₁		476	680	884	Ω
E-to-B resistance	R ₂		7.0	10.0	13.0	kΩ
Turn-on time	ton	Ic = 1.0 A		0.4		μs
Storage time	t stg	Iві = -Iв2 = 10 mA		1.4		μs
Fall time	tf	Vcc = 20 V, R _L = 20 Ω		0.5		μs

^{**} Pulse test PW \leq 350 μ s, duty cycle \leq 2 %

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, contact an NEC sales representative.

[MEMO]

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